CoolMOS™ Power Transistor

Features

- Low gate charge
- Extreme dv/dt rated
- High peak current capability
- Qualified for industrial grade applications according to JEDEC[1)]
- Pb-free lead plating; RoHS compliant; Halogen free mold compound

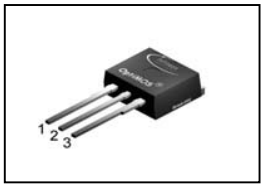
Product Summary

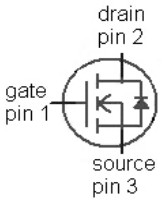
V_{DS}	650	V
$R_{DS(on),max}$	0.28	Ω
$Q_{g,typ}$	63	nC

CoolMOS C3 designed for:

- Notebook Adapter

TO-262-3-1





Type	Package	Marking
SPI15N65C3	P-TO262-3-1	15N65C3

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25 °C	15	A
		T_C=100 °C	9.4	
Pulsed drain current[3)]	$I_{D,pulse}$	T_C=25 °C	45	
Avalanche energy, single pulse	E_{AS}	I_D=3 A, V_{DD}=50 V	460	mJ
Avalanche energy, repetitive t_{AR}[2),3)]	E_{AR}	I_D=5 A, V_{DD}=50 V	0.8	
Avalanche current, repetitive t_{AR}[3),4)]	I_{AR}		5.0	A
MOSFET dv/dt ruggedness	dv/dt	V_{DS}=0...480 V	50	V/ns
Gate source voltage	V_{GS}	static	±20	V
		AC (f>1 Hz)	±30	
Power dissipation	P_{tot}	T_C=25 °C	156	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current[2)]	I_S	T_C=25 °C	15	A
Diode pulse current[3)]	$I_{S,pulse}$		45	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	0.8	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	62	
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	1.6 mm (0.063 in.) from case for 10 s	-	-	260	°C
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=250 µA	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.675 mA	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	V_{DS}=600 V, V_{GS}=0 V, T_j=25 °C	-	0.5	25	µA
		V_{DS}=600 V, V_{GS}=0 V, T_j=150 °C	-	25	-	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=9.4 A, T_j=25 °C	-	0.25	0.28	Ω
		V_{GS}=10 V, I_D=9.4 A, T_j=150 °C	-	0.68	-	
Gate resistance	R_G	f=1 MHz, open drain	-	1.4	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=25 V, f=1 MHz	-	1600	-	pF
Output capacitance	C_{oss}		-	540	-	
Effective output capacitance, energy related[5)]	$C_{o(er)}$	V_{GS}=0 V, V_{DS}=0 V to 480 V	-	67	-	
Effective output capacitance, time related[6)]	$C_{o(tr)}$		-	120	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=400 V, V_{GS}=10 V, I_D=15 A, R_G=6.8 Ω	-	32	-	ns
Rise time	t_r		-	14	-	
Turn-off delay time	$t_{d(off)}$		-	70	-	
Fall time	t_f		-	11	-	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=480 V, I_D=15 A, V_{GS}=0 to 10 V	-	9	-	nC
Gate to drain charge	Q_{gd}		-	29	-	
Gate charge total	Q_g		-	63		
Gate plateau voltage	$V_{plateau}$		-	5.4	-	V
Reverse Diode						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=15 A, T_j=25 °C	-	1.0	1.2	V
Reverse recovery time	t_{rr}	V_R=480 V, I_F=I_S, di_F/dt=100 A/µs	-	420	-	ns
Reverse recovery charge	Q_{rr}		-	8	-	µC
Peak reverse recovery current	I_{rrm}		-	32	-	A

[1)] J-STD20 and JESD22

[2)] Limited only by maximum temperature.

[3)] Pulse width t_p limited by $T_{j,max}$

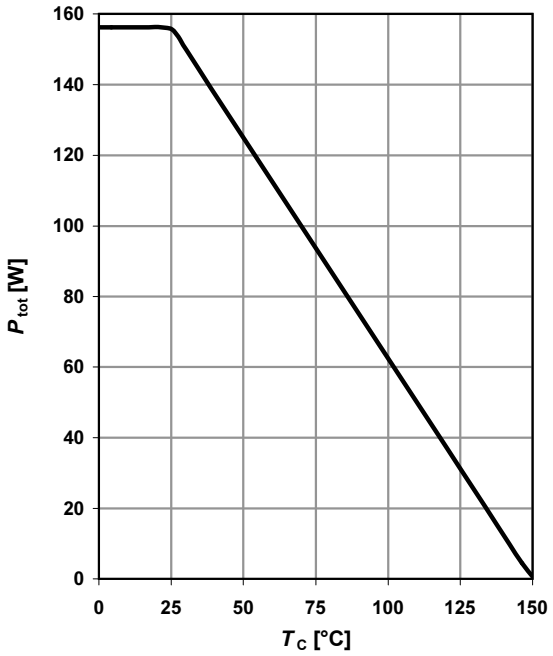
[4)] Repetitive avalanche causes additional power losses that can be calculated as P_{AV}=E_{AR}*f.

[5)] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

[6)] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

1 Power dissipation

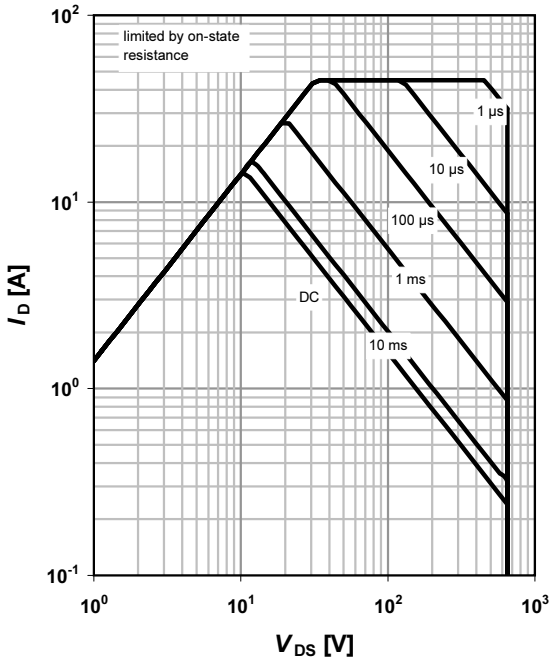
$P_{tot}=f(T_C)$



2 Safe operating area

$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$

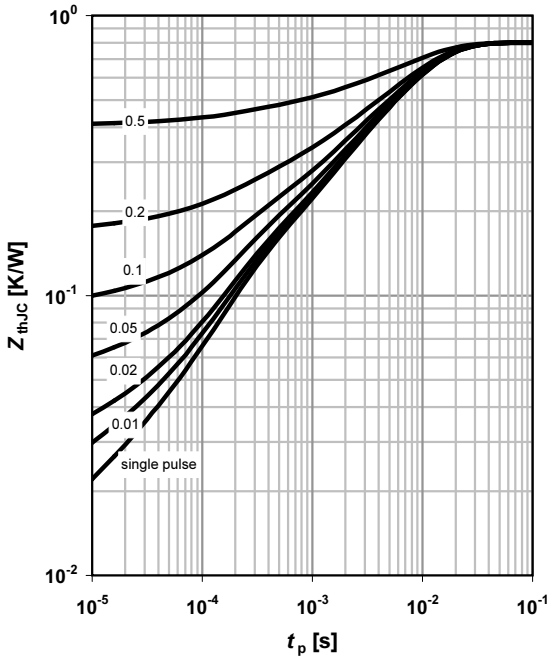
parameter: t_p



3 Max. transient thermal impedance

$Z_{(thJC)}=f(t_p)$

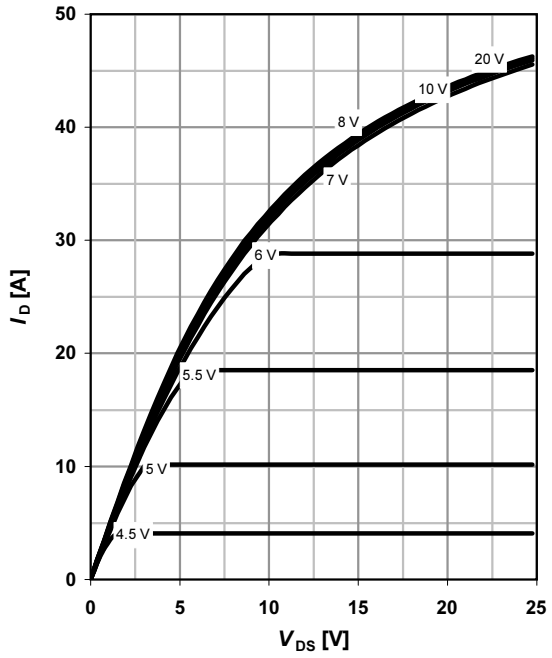
parameter: $D=t_p/T$



4 Typ. output characteristics

$I_D=f(V_{DS})$; $T_j=25$ °C

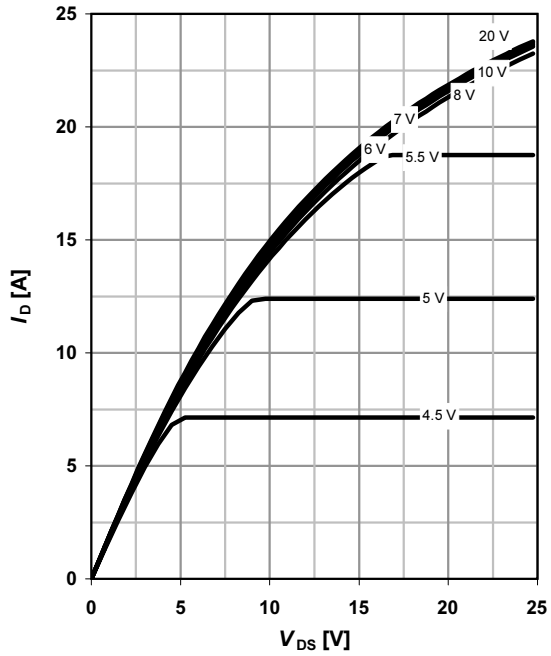
parameter: V_{GS}



5 Typ. output characteristics

I_D=f(V_{DS}); T_j=150 °C

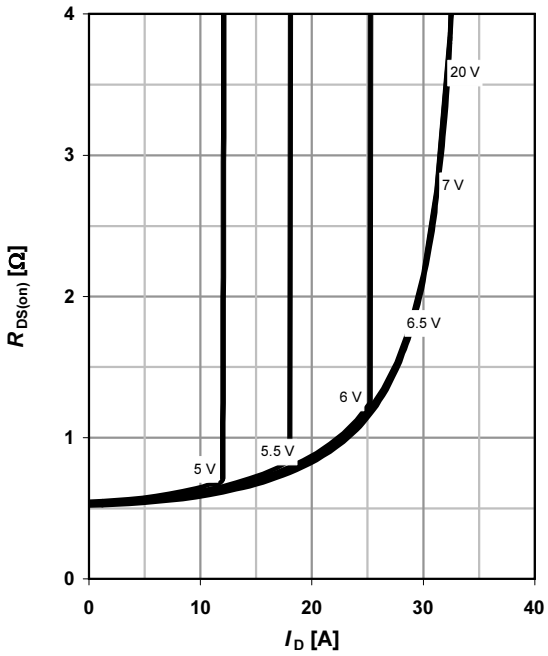
parameter: V_{GS}



6 Typ. drain-source on-state resistance

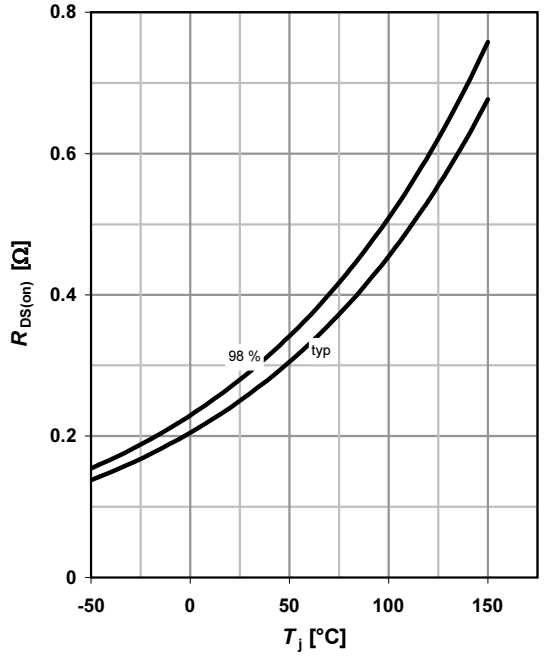
$R_{DS(on)}$=f(I_D); T_j=150 °C

parameter: V_{GS}



7 Drain-source on-state resistance

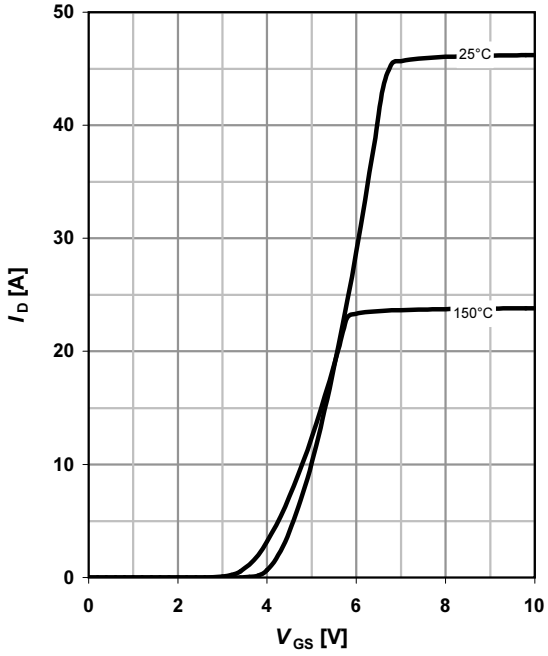
$R_{DS(on)}$=f(T_j); I_D= 9.4 A; V_{GS}=10 V



8 Typ. transfer characteristics

I_D=f(V_{GS}); |V_{DS}|>2|I_D|$R_{DS(on)max}$

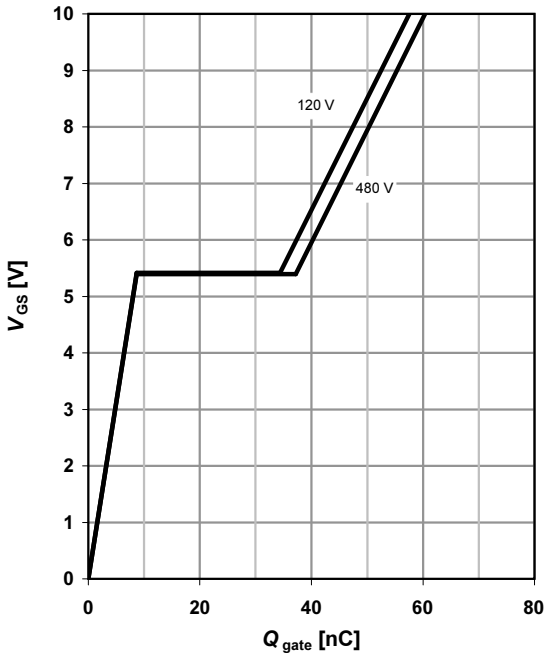
parameter: T_j



9 Typ. gate charge

V_{GS}=f(Q_{gate}); I_D= 15 A pulsed

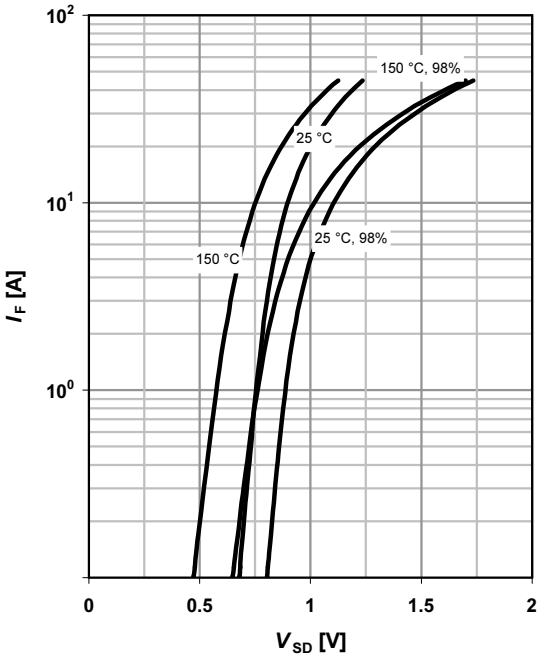
parameter: V_{DD}



10 Forward characteristics of reverse diode

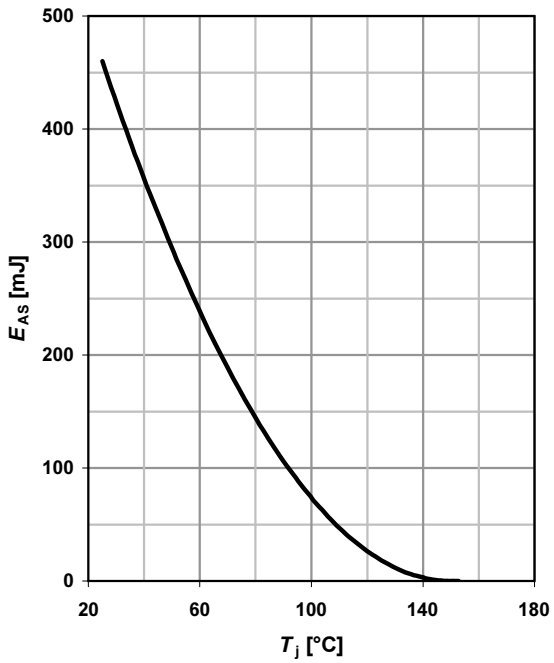
I_F=f(V_{SD})

parameter: T_j



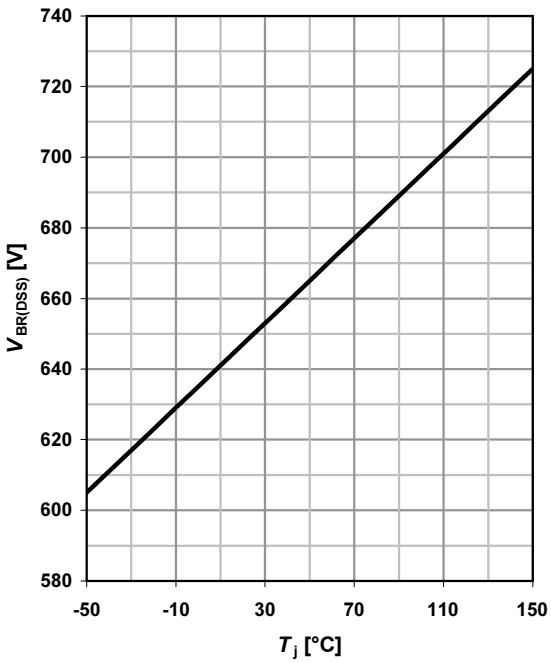
11 Avalanche energy

E_{AS}=f(T_j); I_D=3 A; V_{DD}=50 V



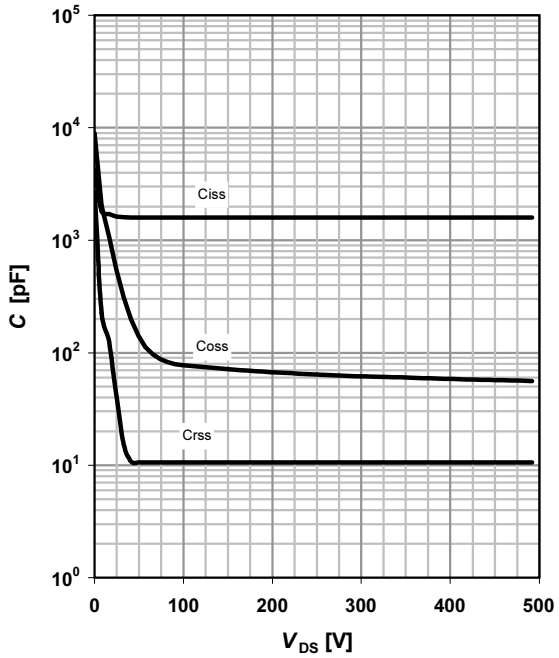
12 Drain-source breakdown voltage

$V_{BR(DSS)}$=f(T_j); I_D=0.25 mA



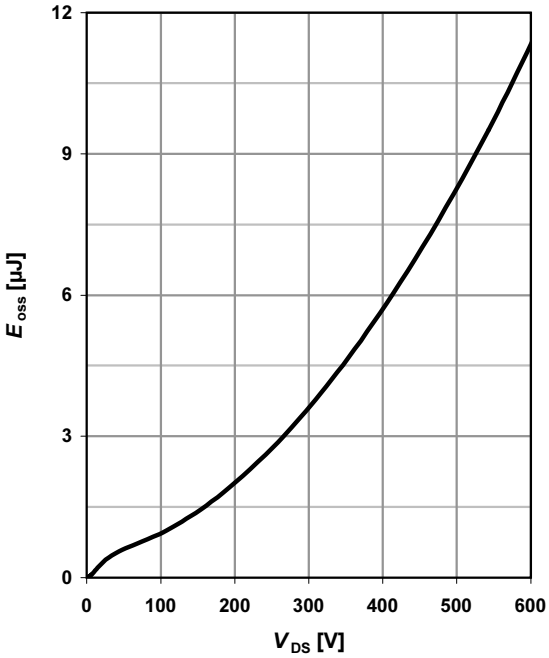
13 Typ. capacitances

C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

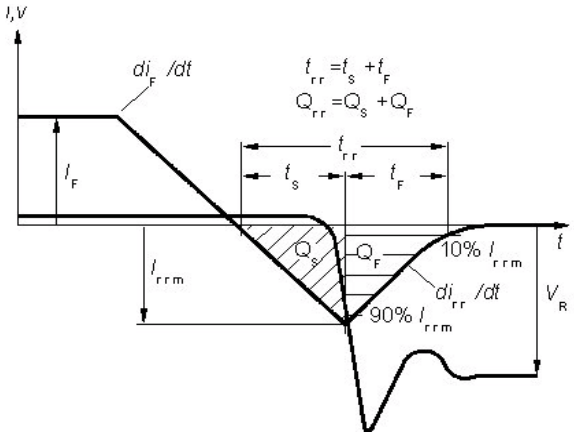


14 Typ. Coss stored energy

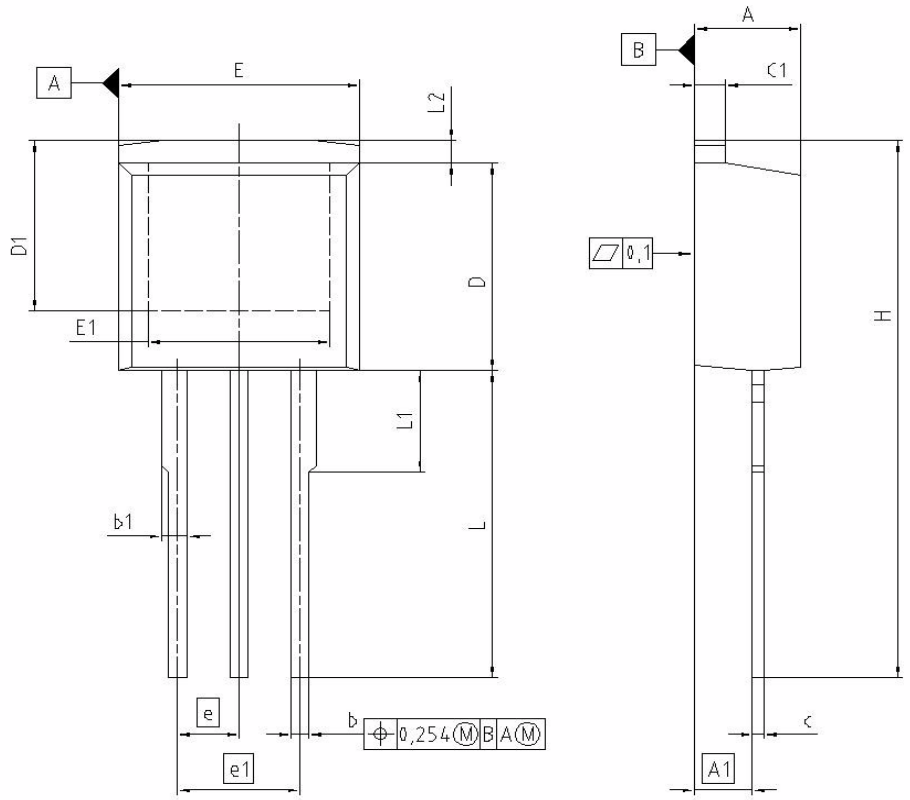
E_{oss}= f(V_{DS})



Definition of diode switching characteristics



PG-TO262-3-1: Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.500	0.169	0.177
A1	2.150	2.650	0.085	0.104
b	0.650	0.850	0.026	0.033
b1	0.635	1.400	0.025	0.055
c	0.400	0.600	0.016	0.024
c1	1.170	1.370	0.046	0.054
D	9.050	9.450	0.356	0.372
D1	6.900	7.650	0.272	0.301
E	9.800	10.200	0.386	0.402
E1	7.250	8.600	0.285	0.339
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
L	13.000	14.000	0.512	0.551
L1	4.350	4.750	0.171	0.187
L2	0.700	1.300	0.028	0.051

REFERENCE JEDEC TO262
SCALE 0 2.5 5mm
EUROPEAN PROJECTION
ISSUE DATE 01-06-2005
FILE TO262_1

Dimensions in mm/inches:

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